

ASSP
BIPOLAR

SWITCHING REGULATOR CONTROLLER

MB3775

■ LOW VOLTAGE DUAL PWM SWITCHING REGULATOR CONTROLLER

The MB3775 is a dual pulse-width-modulation control circuit. It contains the basic circuits required for two PWM control circuits. Complete synchronization is obtained by using the same oscillator output waveform. This IC can provide following types of output voltage: step down, step up, and inverter. Power consumption is low, thus the MB3775 is ideal for use in high-efficiency portable equipment.

■ FEATURES

- Wide supply voltage range: 3.6 V to 18 V
- Low current consumption: 1.3 mA typical
- Wide oscillation frequency range: 1 kHz to 500 kHz
- On-chip timer latch short protection circuit
- On-chip under voltage lockout protection
- On-chip reference voltage: 1.28 V
- Variable dead time provides control over total operating range.
- Two types of packages (SOP-16pin : 1 type, SSOP-16pin : 1 type)

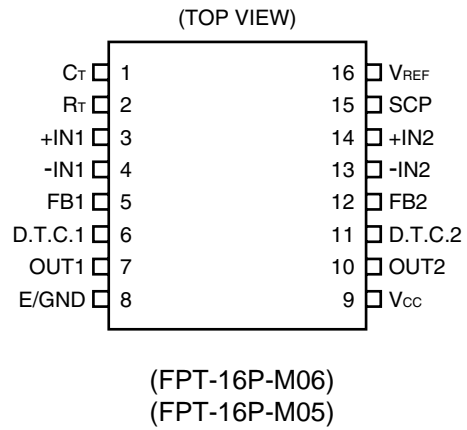
■ APPLICATIONS

- LCD monitor/panel
- Surveillance camera etc.

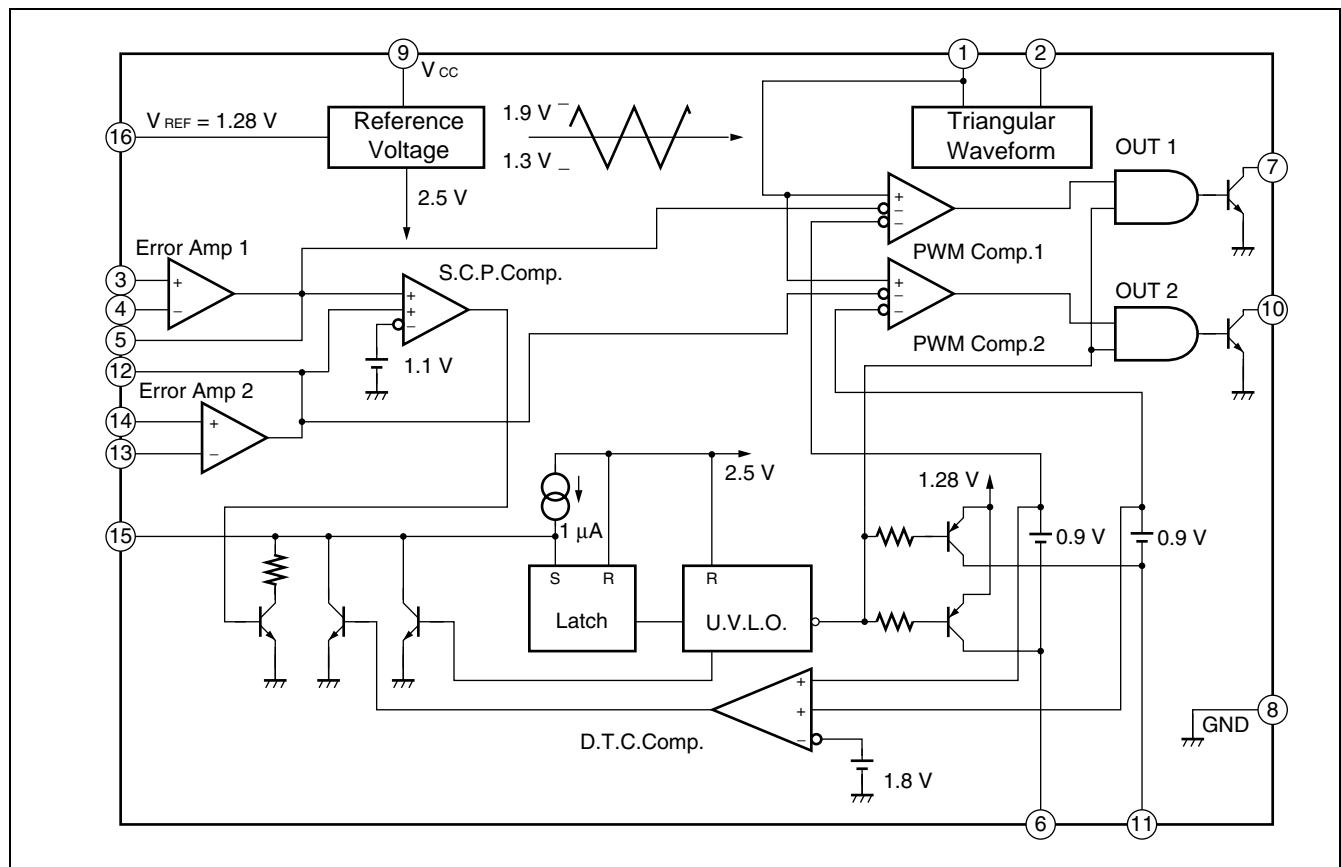
MB3775

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■ PIN ASSIGNMENT



■ BLOCK DIAGRAM



■ OPERATION DESCRIPTION

1. Reference voltage

The reference voltage circuit generates a stable, temperature-compensated 2.5 V reference from V_{CC} terminals (pin 9) for use by internal circuits.

A reference voltage of temperature compensated 1/2 V_{REF} can be obtained to external circuit by V_{REF} terminal (pin 16).

2. Oscillator

A triangular waveform of any frequency is obtained by connecting an external capacitor and resistor to the C_T terminal (pin 1) and R_T terminals (pin 2).

The amplitude of this waveform is from 1.3 V to 1.9 V. The oscillator is internally connected to the non-inverting inputs of the PWM comparators. The oscillator waveform is available at the C_T terminal (pin 1).

3. Error amplifiers

The error amplifier detects the output voltage of the switching regulator.

The common-mode input voltage range is -0.2 V to 1.45 V, so the input reference voltage can be set the V_{REF} terminal (pin 16) and GND terminal levels. Error amplifiers can be used as either inverting and non-inverting amplifiers.

The voltage gain is fixed. Phase compensation is possible by connecting a capacitor to the FB terminals (pins 5 and 12) of the error amplifiers.

The error amplifier output are internally connected to the inverting inputs of the PWM comparators and also to the short protection circuit.

4. Timer latch short protection circuit

The timer latch short protection circuit detects the output levels of the error amplifiers. If one or both error amplifier outputs are 1.1 V or lower, the timer circuit begins charging the externally connected protection enable capacitor. If the output level of the error amplifier does not drop below the normal voltage range before the capacitor voltage reaches the transistor base-emitter voltage V_{BE} (\approx 0.65 V), the latch circuit turns the output drive transistor off and sets the dead time to 100 %.

5. Under voltage lockout protection circuit

An ambiguous transition state at power-on or a momentary fluctuation in the supply line may result in loss of control and may adversely affect or even destroy the system. The under voltage lockout protection circuit compares the internal reference voltage level with the supply voltage level. If the supply voltage level falls below the reference level the latch circuit is reset the output drive transistor is turned off and the dead time is set to 100%. The protection enable terminal (pin 15) is pulled "Low".

6. PWM comparator

Each PWM comparator has two inverting inputs and one non-inverting input. This voltage-to-pulse-width converter controls the output pulse width according to the input voltage.

The PWM comparator turns the output drive transistor on when the oscillator triangular waveform is higher than the error amplifier output and the dead time control terminal voltage.

7. Output drive transistor

The open-collector output-drive transistors provide common-emitter output of 18 V dielectric capability. The output drive transistors can source up to 50 mA of drive current to the switching power transistor.

■ ABSOLUTE MAXIMUM RATING

Parameter	Symbol	Condition	Rating		Unit
			Min	Max	
Power Supply Voltage	V _{CC}	—	—	20	V
Error Amp Input Voltage	V _I	—	-0.3	+10	V
Collector Output Voltage	V _O	—	—	20	V
Collector Output Current	I _O	—	—	75	mA
Power Dissipation	P _D	T _a ≤ +25 °C(SOP)	—	*620	mW
		T _a ≤ +25 °C(SSOP)	—	*430	mW
Operating Ambient Temperature	T _a	—	-30	+85	°C
Storage temperature	T _{stg}	—	-55	+125	°C

*: The packages are mounted on the epoxy board (4 cm x 4 cm x 1.5 mm).

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Power Supply Voltage	V _{CC}	3.6	6.0	18	V
Error Amp Input Voltage	V _I	-0.2	—	+1.45	V
Collector Output Voltage	V _O	—	—	18	V
Collector Output Current	I _O	0.3	—	50	mA
Phase Compensation Capacitor	C _P	—	0.1	—	μF
Timing Capacitor	C _T	150	—	15000	pF
Timing Resistor	R _T	5.1	—	100	kΩ
Oscillator Frequency	f _{OSC}	1	—	500	kHz
Reference Voltage Output Current	I _{REF}	-3	-1	—	mA
Operating Ambient Temperature	T _a	-30	+25	+85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

(Ta = +25 °C, VCC = 6 V)

Parameter		Condition	Symbol	Value			Unit
				Min	Typ	Max	
Reference Section	Output Voltage	I _{OR} = -1 mA	V _{REF}	1.26	1.28	1.30	V
	Output Temp. Stability	Ta = -30 °C to +85 °C	V _{RTC}	-2	±0.2	+2	%
	Input Stability	VCC = 3.6 V to 18 V	Line	—	2	10	mV
	Load Stability	I _{OR} = -0.1 mA to -1 mA	Load	—	1	7.5	mV
	Short Circuit Output Current	V _{REF} = 0 V	I _{OS}	—	-30	-10	mA
Under Voltage Lockout Protection Section	Threshold Voltage	I _{OR} = -0.1 mA	V _{tH}	—	2.72	—	V
		I _{OR} = -0.1 mA	V _{tL}	—	2.60	—	V
	Hysteresis Width	I _{OR} = -0.1 mA	V _{HYS}	80	120	—	mV
	Reset Voltage (V _{CC})	—	V _R	1.5	1.9	—	V
Protection Circuit Section	Input Threshold Voltage	—	V _{tPC}	0.60	0.65	0.7	V
	Input Stand by Voltage	No pull up	V _{STB}	—	50	100	mV
	Input Latch Voltage	No pull up	V _I	—	50	100	mV
	Input Source Current	—	I _{bpc}	-1.4	-1.0	-0.6	μA
	Comparator Threshold Voltage	Pin 5, Pin 12	V _{tC}	—	1.1	—	V
Triangular Waveform Oscillator Section	Oscillator Frequency	C _T = 330 pF, R _T = 15 kΩ	f _{osc}	—	200	—	kHz
	Frequency Deviation	C _T = 330 pF, R _T = 15 kΩ	f _{dev}	—	10	—	%
	Frequency Stability (V _{CC})	VCC = 3.6 V to 18 V	f _{dV}	—	1	—	%
	Frequency Stability (Ta)	Ta = -30 °C to +85 °C	f _{dT}	-4	—	+4	%
Dead-Time Control Section	Input Threshold Voltage (f _{osc} = 10 kHz)	Duty Cycle = 0 %	V _{t0}	—	1.0	V _{REF} - 0.15	V
		Duty Cycle = 100 %	V _{t100}	0.2	0.4	—	V
	Input Bias Current	—	I _{bdT}	—	-0.2	-1	μA
	Latch Mode Source Current	V _{dt} = 0.7 V	I _{dt}	—	-150	-80	μA
	Latch Input Voltage	I _{dt} = -40 μA	V _{dt}	V _{REF} - 0.1	—	—	V

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MB3775

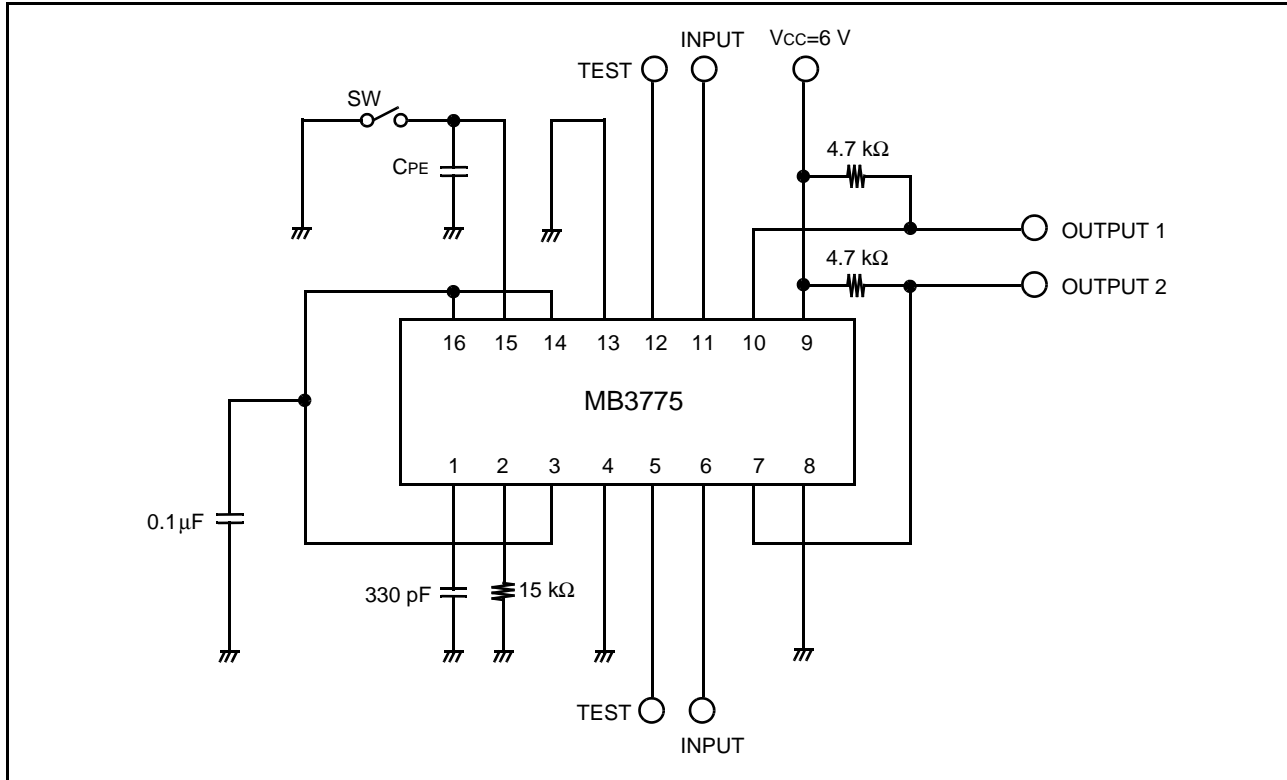
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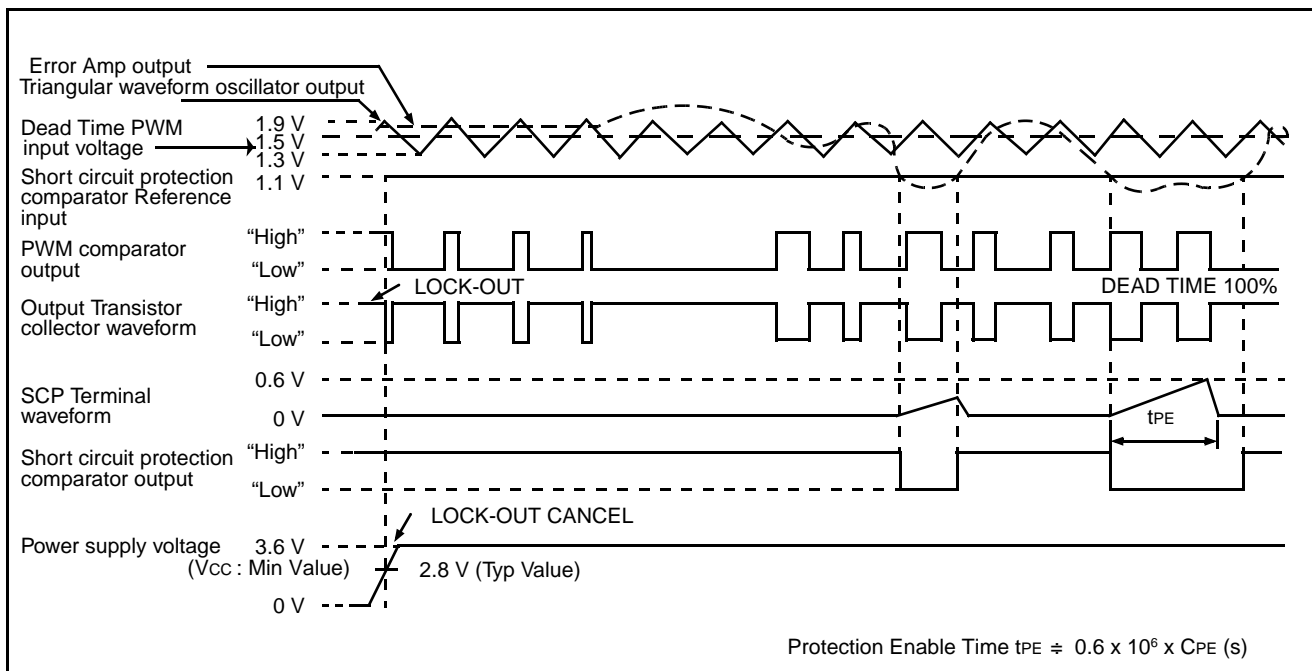
(Ta = +25 °C, Vcc = 6 V)

Parameter		Condition	Symbol	Value			Unit
				Min	Typ	Max	
Error Amp Section	Input Offset Voltage	Vo = 1.6 V	V _{IO}	-10	—	+10	mV
	Input Offset Current	Vo = 1.6 V	I _{IO}	-100	—	+100	nA
	Input Bias Current	Vo = 1.6 V	I _B	-500	-100	—	nA
	Common Mode Input Voltage Range	Vcc = 3.6 V to 18 V	V _{ICR}	-0.2	—	+1.45	V
	Voltage Gain		A _v	84	120	—	V/V
	Frequency Band Width	A _v = -3 dB	BW	—	3	—	MHz
	Common Mode Rejection Ratio		CMRR	60	80	—	dB
	Max Output Voltage Width		V _{OM+}	2.2	2.4	—	V
			V _{OM-}	-	0.7	0.9	V
	Output Sink Current	Vo = 1.6 V	I _{OM+}	24	50	—	μA
	Output Source Current	Vo = 1.6 V	I _{OM-}	—	-1.2	-0.7	mA
PWM Com-parator Section	Input Threshold Voltage (fosc=10 kHz)	Duty Cycle = 0 %	V _{t0}	—	1.9	2.1	V
		Duty Cycle = 100 %	V _{t100}	1.05	1.3	—	V
	Input Sink Current	Pin 5, Pin 12 = 1.6 V	I _{IN+}	24	50	—	μA
	Input Source Current	Pin 5, Pin 12 = 1.6 V	I _{IN-}	—	-1.2	-0.7	mA
Output Section	Output Leak Current	Vo = 18 V	Leak	—	—	10	μA
	Output Saturation Voltage	I _o = 50 mA	V _{SAT}	—	1.1	1.4	V
Stand by Current		Output "OFF"	I _{CCS}	—	1.3	1.8	mA
Average Supply Current		R _T = 15 kΩ	I _{CCa}	—	1.7	2.4	mA

■ TEST CIRCUIT



■ TIMING CHART (Internal Waveform)



APPLICATION CIRCUIT

Fig. 1 - Chopper Type Step Down/Inverting

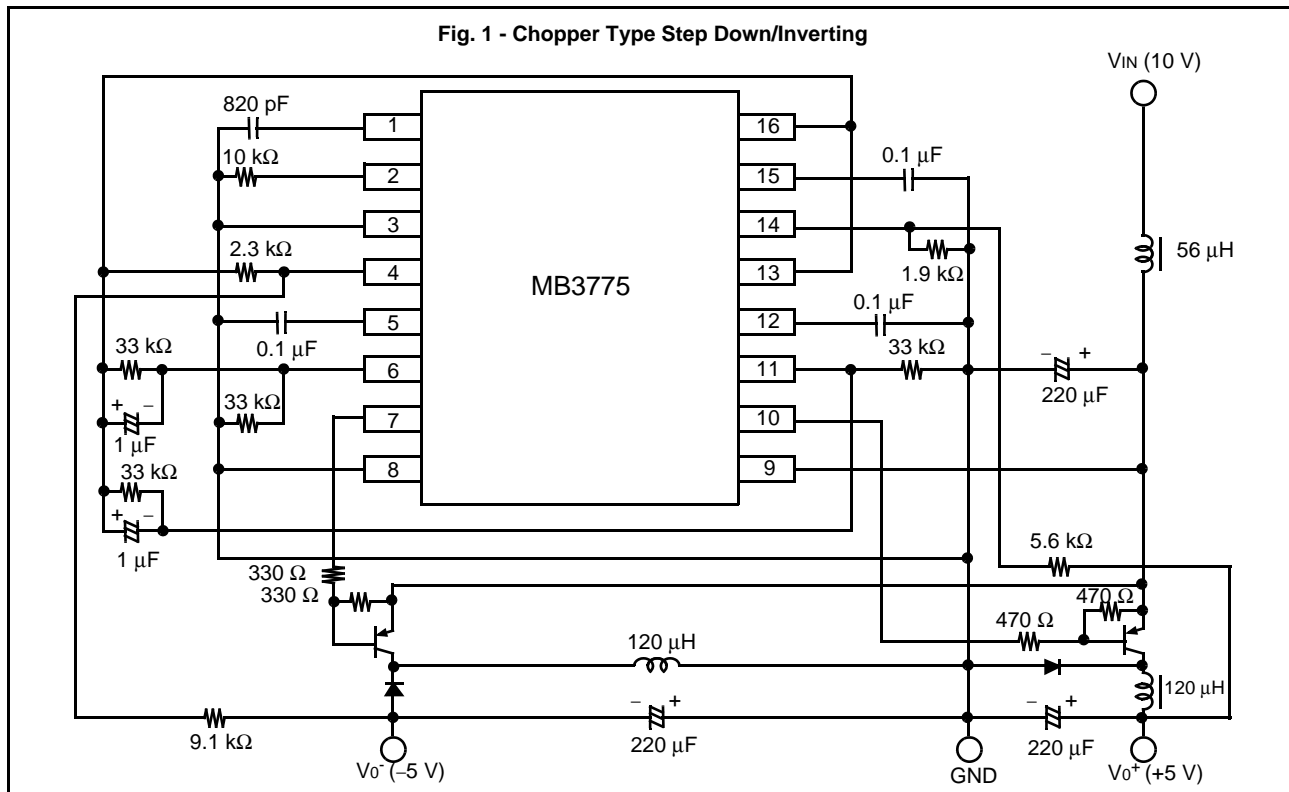
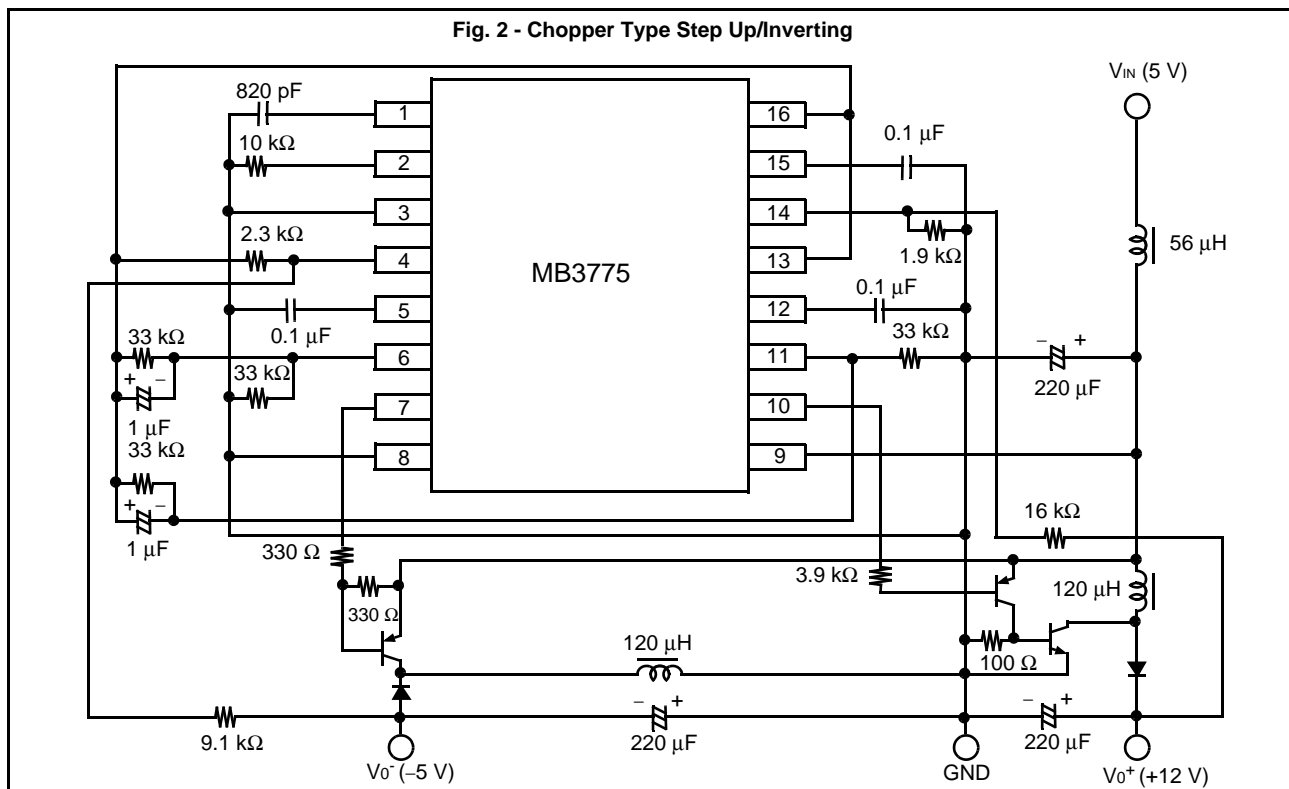
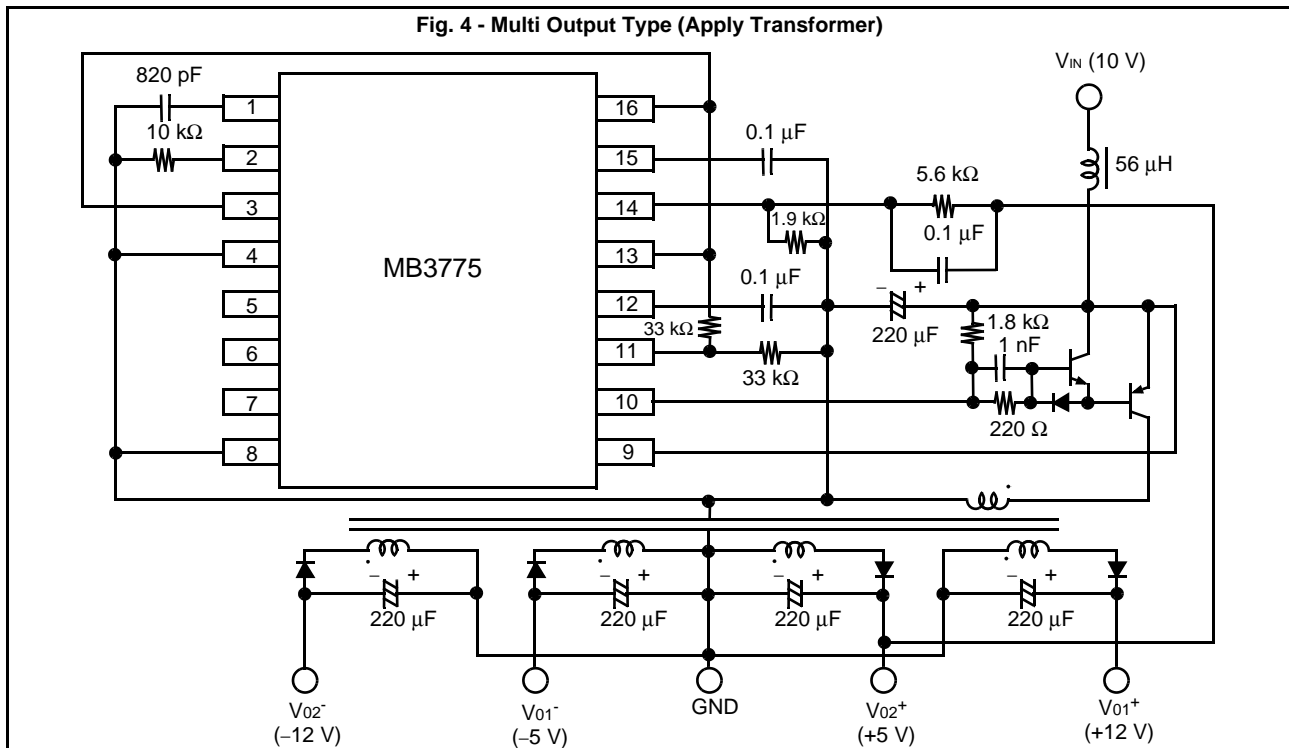


Fig. 2 - Chopper Type Step Up/Inverting



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Fig. 3 - Chopper Type Step Up/Inverting (For High Speed)



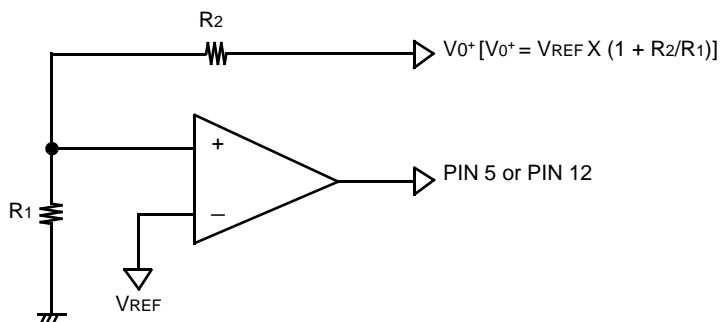
■ HOW TO SET OUTPUT VOLTAGE

The output voltage is set using the connection shown in Fig. 5 and 6.

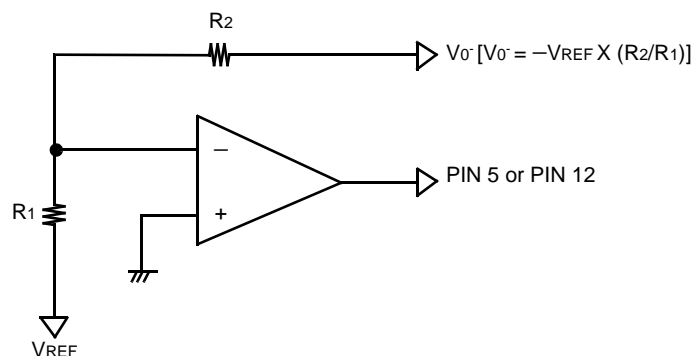
The error amplifiers are supplied to the internal reference voltage circuit as are the other internal circuits. The common-mode input voltage range is from -0.2 V to $+1.45\text{ V}$.

When the amplifiers are operated non-inverting, tie the inverting terminal to V_{REF} ($\approx 1.28\text{ V}$). When the amplifiers are operated inverting, tie the non-inverting terminal to ground.

**Fig. 5 -Connection of Error Amp
Output Voltage V_0 is plus**



**Fig. 6 -Connection of Error Amp
Output Voltage V_0 is minus**



■ HOW TO SET TIME CONSTANT FOR TIMER LATCH SHORT PROTECTION CIRCUIT

TIMING CHART shows the configuration of the protection latch circuit.

Error amplifier outputs, are internally connected to the non-inverting inputs of the short-circuit protection comparator and are compared with the reference voltage (1.1 V) connected to the inverting input.

When the load condition of the switching regulator is stable, the error amplifier has no output fluctuation. Thus, short-circuit protection control is also kept in balance, and the protection enable terminal (pin 15) voltage is kept at about 50 mV.

If the load condition drastically changes due to a load short-circuit and if low-level signals (1.1 V or lower) are input to the non-inverting inputs of the short-circuit protection comparator from the error amplifiers, the short-circuit protection comparator outputs a "Low" level to turn transistor Q₁ off. The protection enable terminal voltage is discharged, and then the short-circuit protection comparator charges the externally connected protection enable capacitor C_{PE} according to the following formula:

$$V_{PE} = 50 \text{ mV} + t_{PE} \times 10^{-6} / C_{PE}$$

$$0.65 = 50 \text{ mV} + t_{PE} \times 10^{-6} / C_{PE}$$

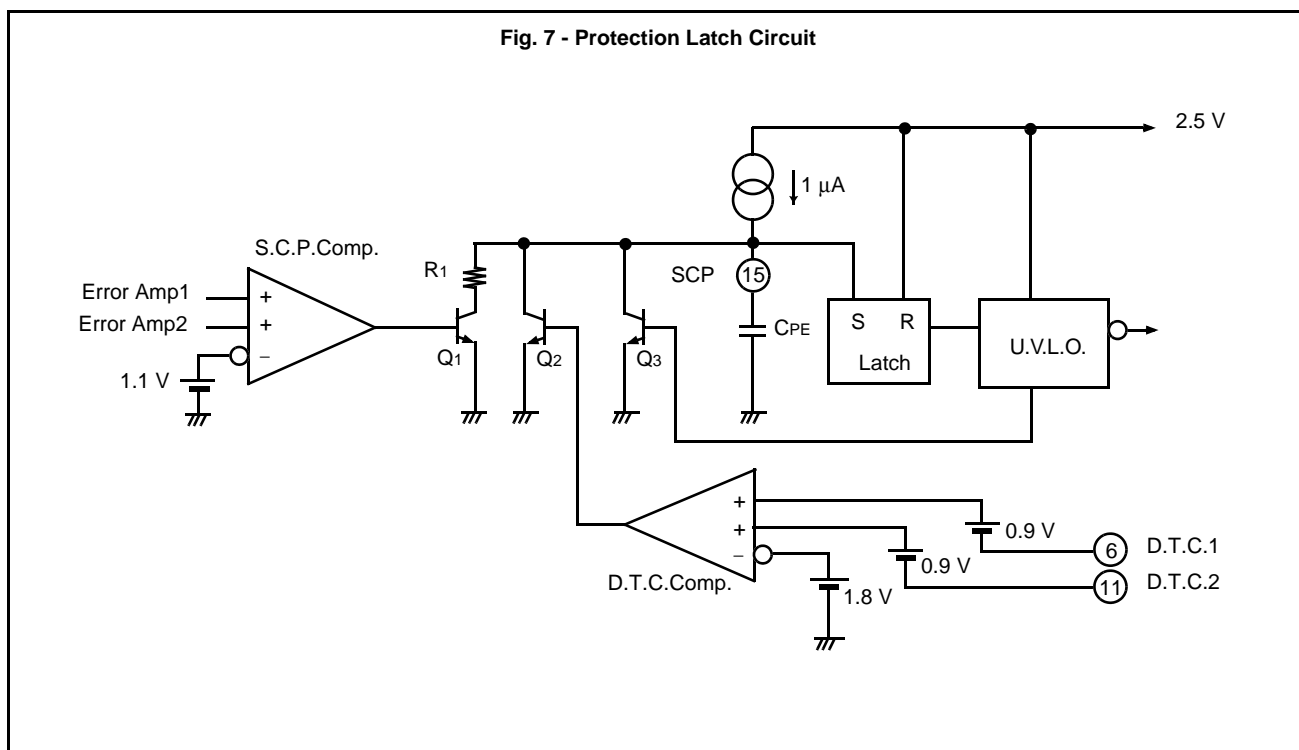
$$C_{PE} = t_{PE} / 0.6 (\mu\text{F})$$

When the protection enable capacitor charges to about 0.65 V, the protection latch is set to enable the under voltage lockout protection circuit and to turn the output drive transistor off. The dead time is set to 100 %.

Once the under voltage lockout protection circuit is enabled, the protection enable is released; however, the protection latch is not reset if the power is not turned off.

The non-inverting inputs of the D.T.C. comparator are connected to the D.T.C. terminals (pins 6 and 11) through the power supply (about 0.9 V) and are compared with a reference voltage (about 1.8 V) connected to the inverting input.

To prevent malfunction of the short protection circuit in soft-start mode (using D.T.C. terminals), the D.T.C. comparator outputs a "High" level to turn Q₂ on until the D.T.C. terminals (pins 6 and 11) voltage drops to about 0.9 V.



■ SYNCHRONIZATION OF ICs

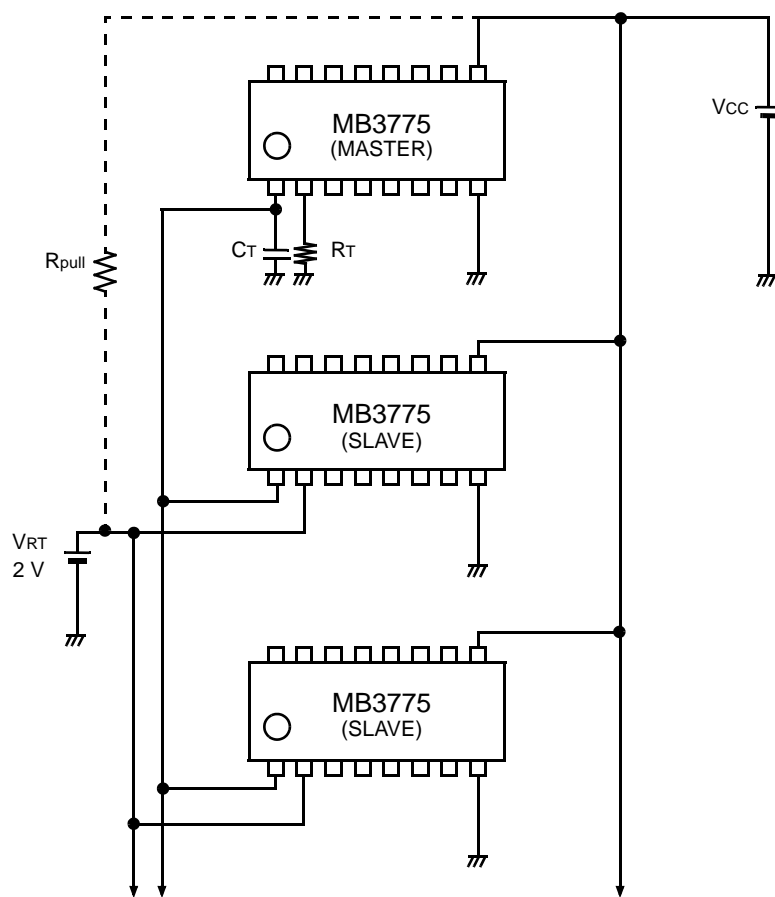
To synchronize MB3775 ICs, first, the specified capacitor and resistor are connected to the C_T and R_T terminals (pins 1 and 2) of the master IC to start self oscillation. Next, 2 V is applied to the R_T terminals (pin 2) of the slave ICs to disable the charge/discharge circuit for triangular wave oscillation. Finally, the C_T terminals (pin 1) of the master and slave ICs are connected.

Instead of applying V_{RT} to the R_T terminals (pin 2), these terminals can be pulled up by a resistor (see resistance indicated by the dashed line in Fig. 8). Select the pull-up resistance R_{pull} from the formula given below.

$$\frac{V_{CC}}{0.5 \times N} \leq R_{pull}$$

R_{pull} : Pull up Resistor (k Ω)
 V_{CC} : Power Supply Voltage (V)
 N : Number of Slave ICs

Fig. 8 - Connection of Master, Slave



■ TYPICAL PERFORMANCE CHARACTERISTICS

Fig. 9 - Reference voltage vs. Power supply voltage

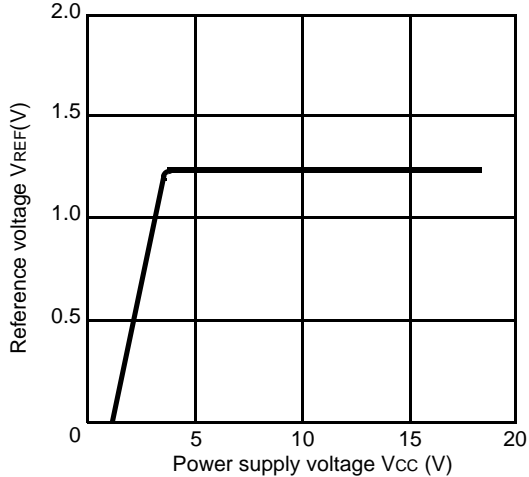


Fig. 10 - Average supply current vs. Power supply voltage

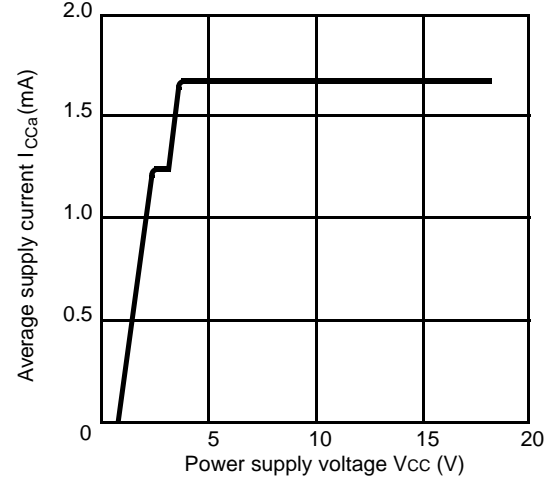


Fig. 11 - Stand by current vs. Power supply voltage

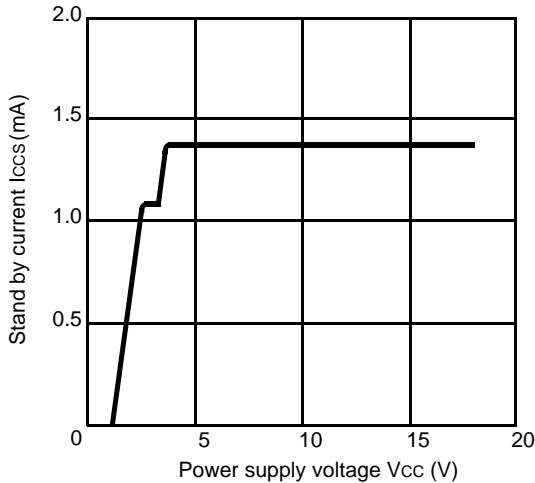


Fig. 12 - Reference voltage vs. Operating ambient temperature

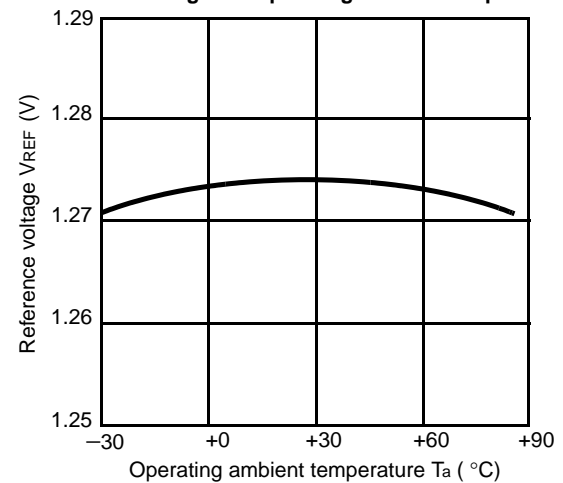


Fig. 13 - Collectorsaturation saturation voltage vs. Sink current

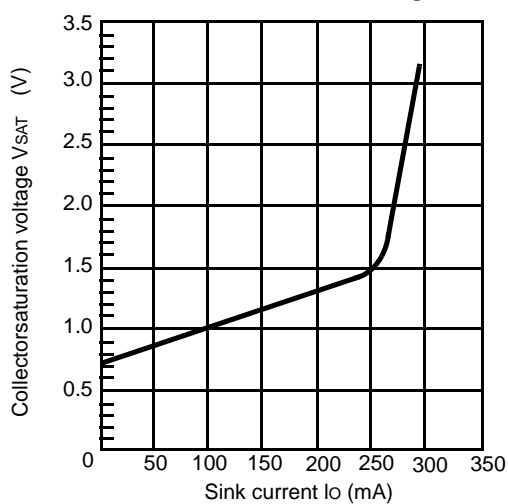
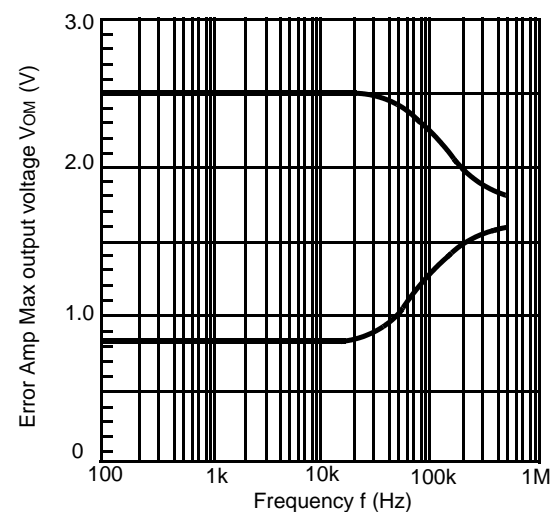


Fig. 14 - Error Amp Max output voltage vs. Frequency



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Fig. 15 - Oscillation Frequency vs. Timing resistor

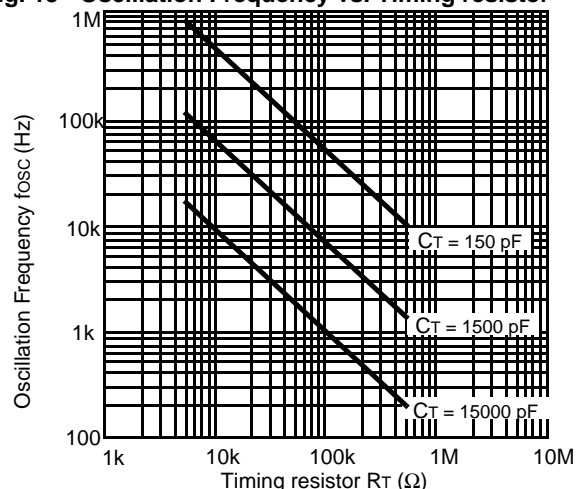


Fig. 16 - Triangular waveform cycle vs. Timing capacitor

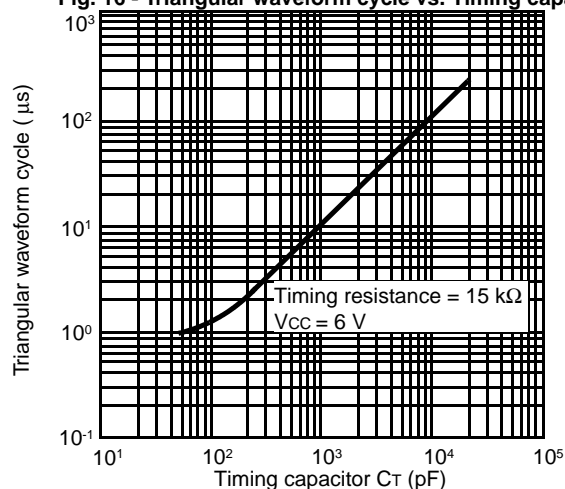


Fig. 17 - Triangular waveform Max Amplitude voltage vs. Timing capacitor

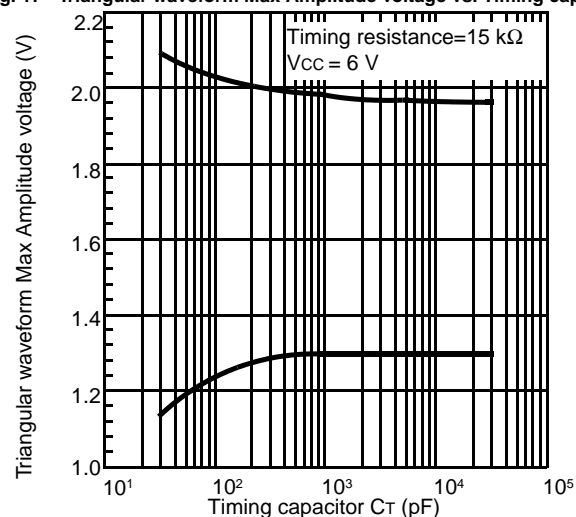


Fig. 18 - Gain/Phase vs. Frequency

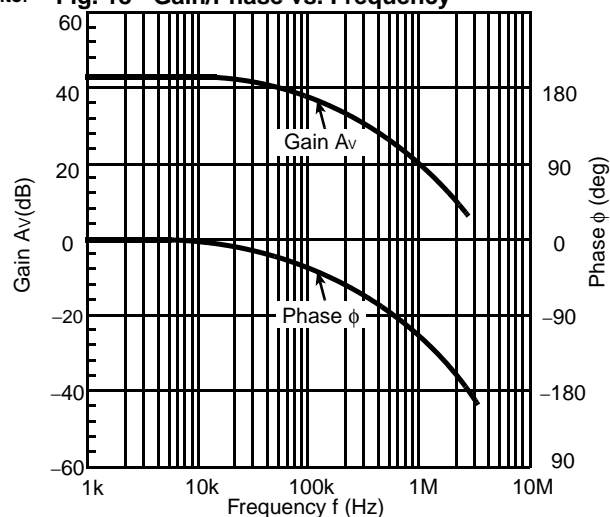


Fig. 19 - Gain/Phase vs. Frequency (Actual Data)

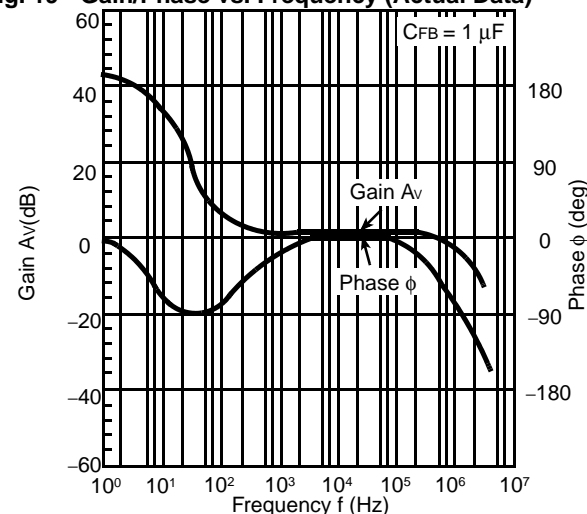
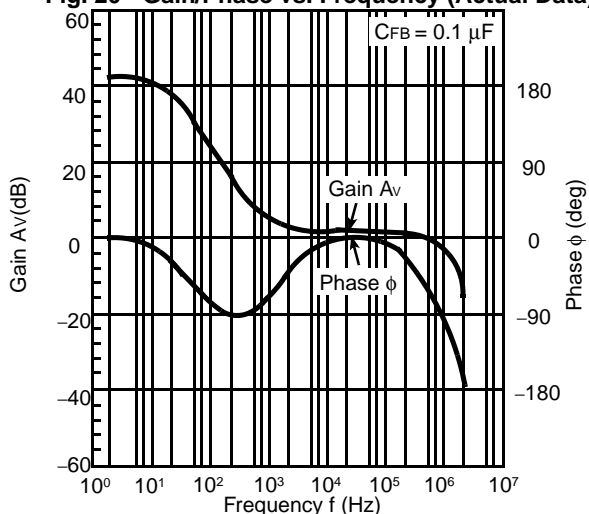
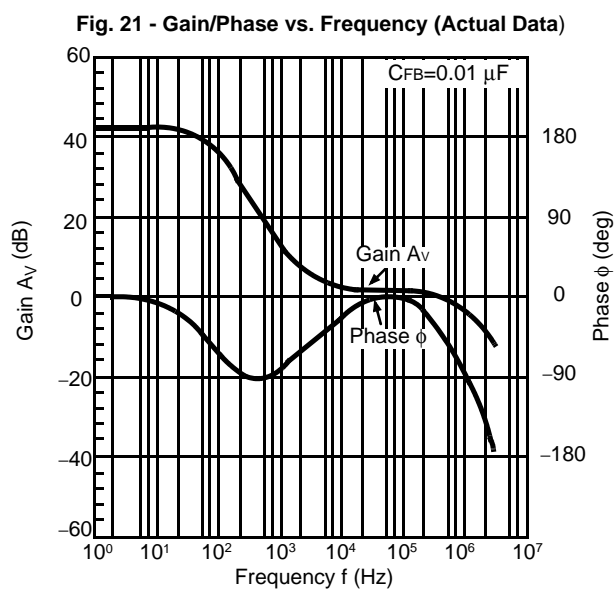


Fig. 20 - Gain/Phase vs. Frequency (Actual Data)



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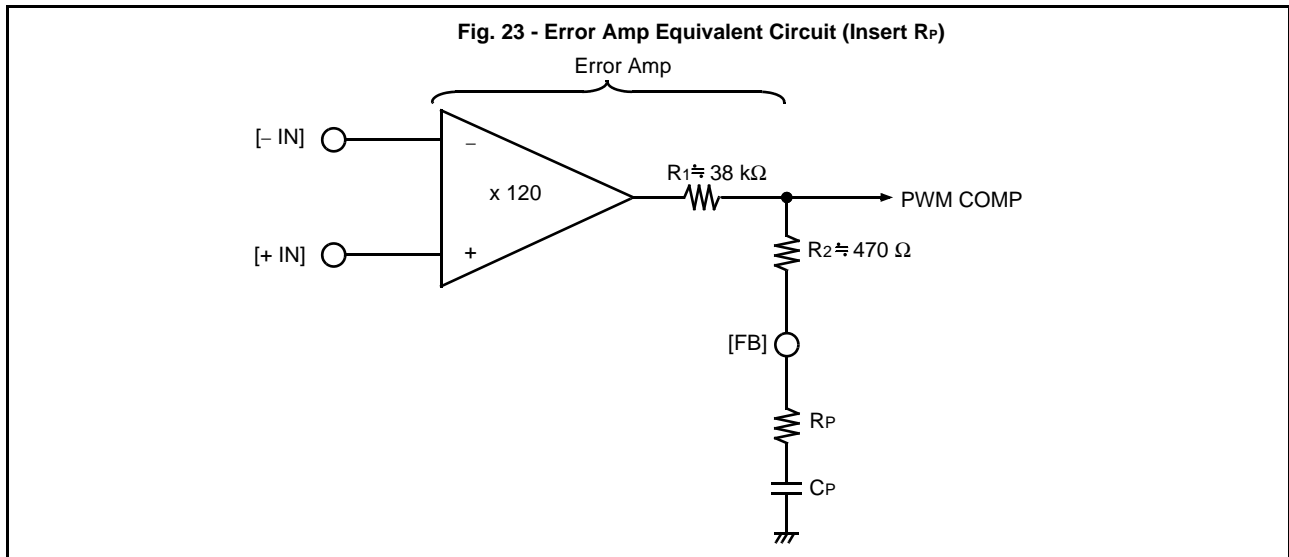
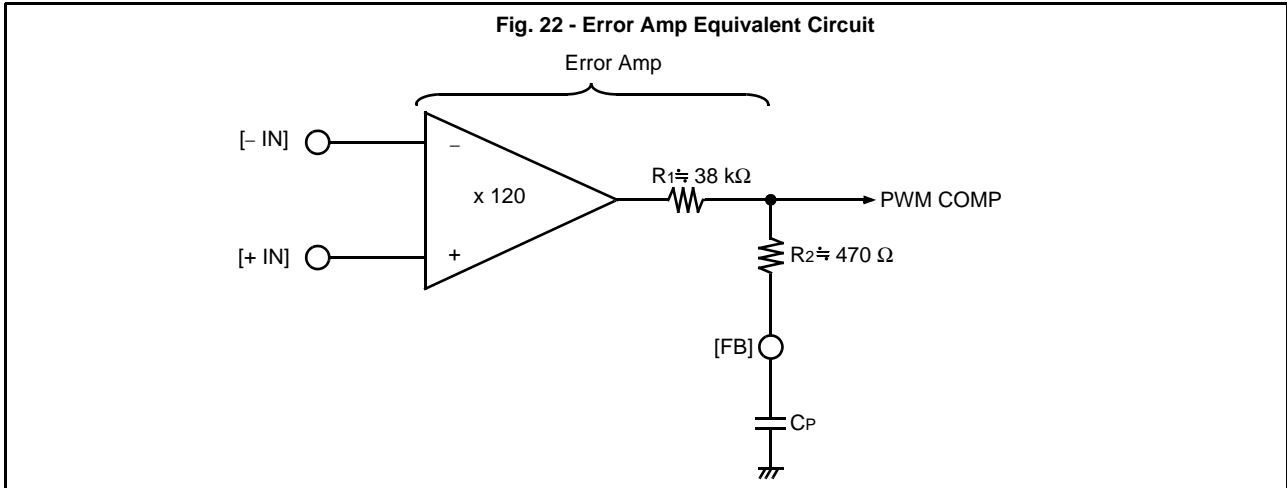
■ HOW TO SET THE ERROR AMPLIFIER FREQUENCY CHARACTERISTIC

Figure 22 shows the equivalent circuit of the error amplifier.

The frequency characteristic of the error amplifier is set by R_1 , R_2 , and C_P . The high-frequency gain is set by the ratio of resistors R_1 and R_2 in the IC (set value ≈ 0 dB).

When $C_P = 0.1 \mu\text{F}$, the gain at $20 \text{ kHz} \leq f \leq 5 \text{ MHz}$ is about 0 dB. The roll-off frequency is adjusted by changing external phase compensating capacitor C_P (see Fig. 24).

When high frequency gain is needed or the phase must be advanced at a low frequency, connect a resistor R_P between the FB terminals (pins 5 and 12) and C_P as shown in Figure 23 (see Fig. 25).



Note: As shown above, the frequency characteristic of the error amplifier is set by the external phase compensating capacitor C_P .

When a ceramic chip capacitor must be used to meet the requirements of a small system, be careful of its temperature characteristic. ($-30^\circ\text{C} \approx 1/5$ and $+80^\circ\text{C} \approx 1/3$ for the frequency characteristic, so a sufficient phase margin must be allowed for at room temperature.) Ceramic chip capacitors with a low temperature characteristic (B characteristic) or film capacitors are recommended (see Fig. 26 to 28).

Fig. 24 - Error Amp Frequency characteristics

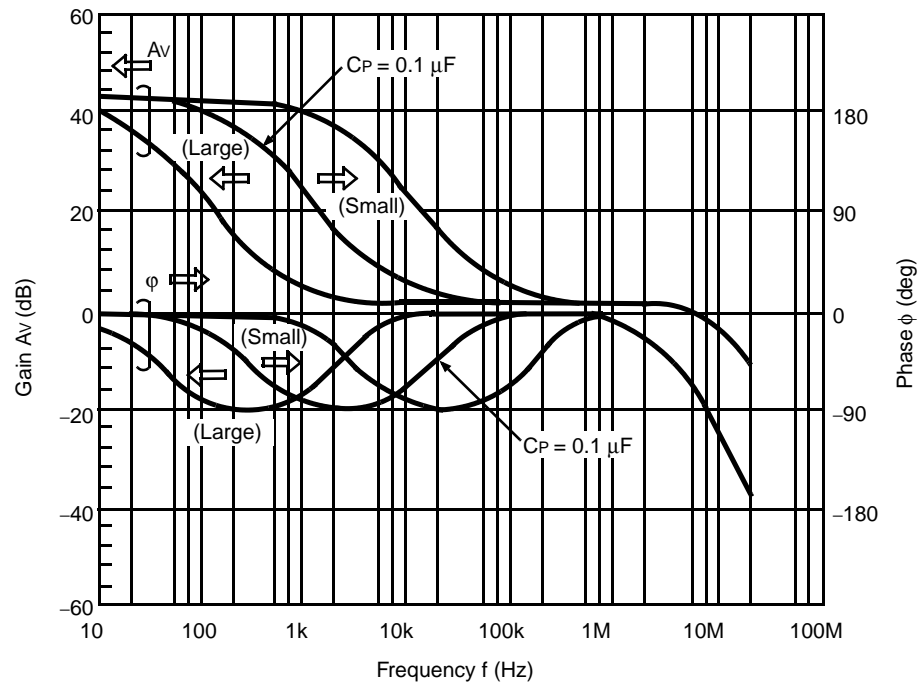


Fig. 25 - Error Amp Frequency characteristics

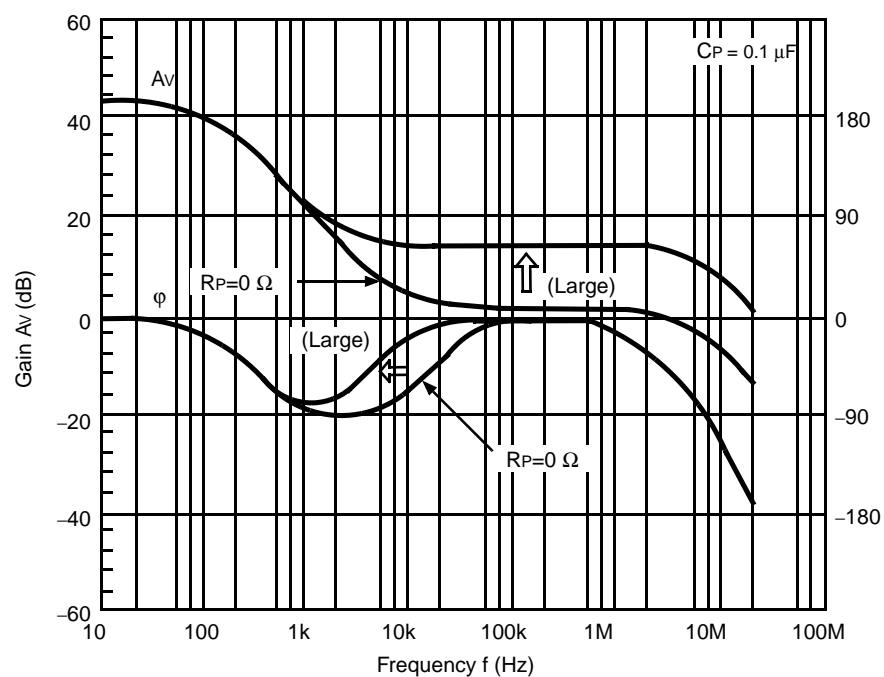


Fig. 26 - Ceramic Chip Capacitor (0.1 μ F)

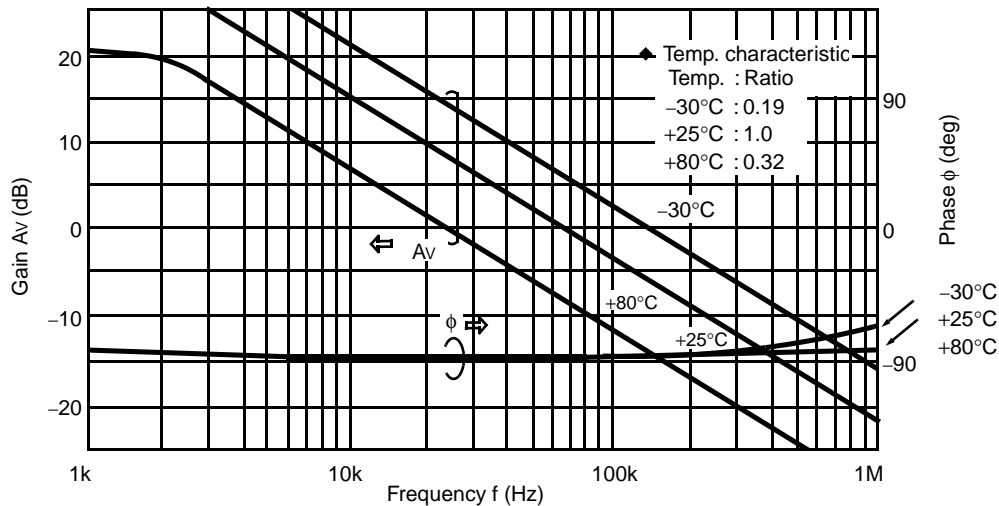


Fig. 27 - Tantal Capacitor (0.33 μ F)

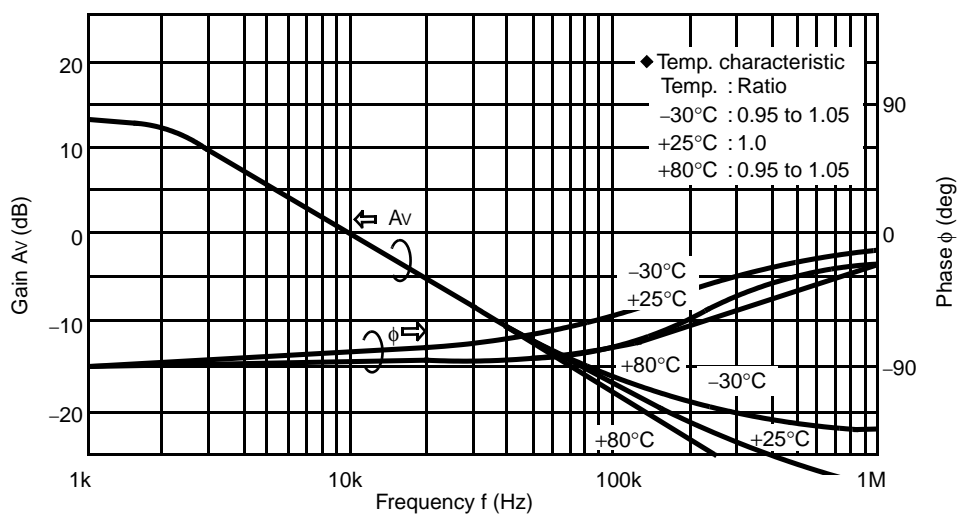
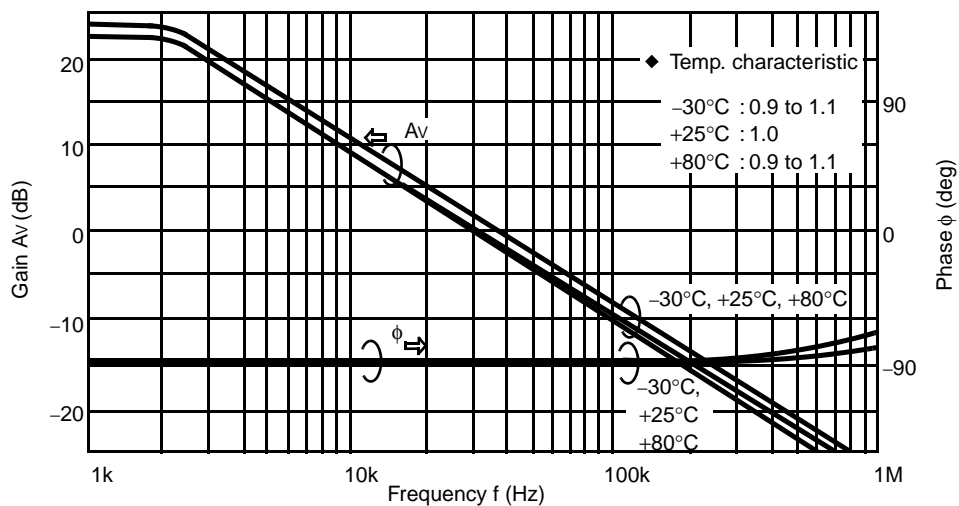


Fig. 28 - Film Capacitor (0.1 μ F)



■ EFFECT OF EQUIVALENT SERIES RESISTANCE OF SMOOTHING CAPACITOR

The equivalent series resistance (ESR) of the smoothing capacitor in the DC/DC converter greatly affects the loop phase characteristic.

A smoothing capacitor with a low ESR reduces system stability by increasing the phase shift in the high-frequency region (see Fig. 30). Therefore, a smoothing capacitor with a high ESR will improve system stability. Be careful when using low ESR semiconductor electrolytic capacitors (OS-CON™) and tantalum capacitors.

Note: OS-CON is the trademark of Sanyo Electric Co., Ltd.

Fig. 29 - Step Down DC/DC Converter Basic Circuit

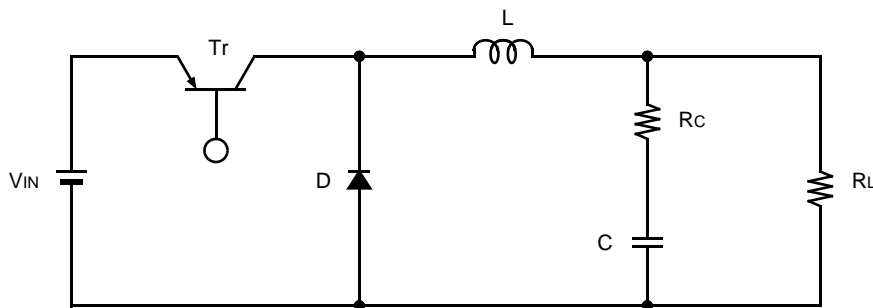


Fig. 30 - Gain vs. Frequency

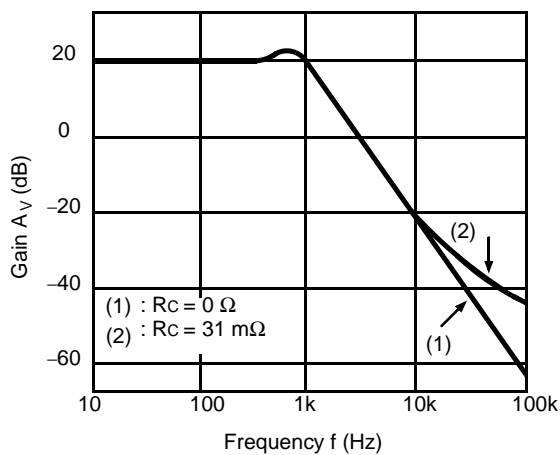
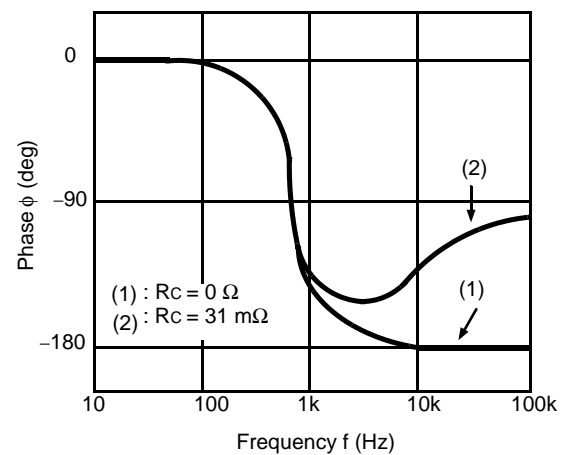


Fig. 31 - Phase vs. Frequency



Reference data

If an aluminum electrolytic smoothing capacitor ($R_C \cong 1.0 \Omega$) is replaced with a low ESR semiconductor electrolytic capacitor (OS-CON™: $R_C \cong 0.2 \Omega$), the phase shift is reduced by half (see Fig. 33 and 34).

Fig. 32 - DC/DC Converter A_v vs. ϕ characteristic Test Circuit

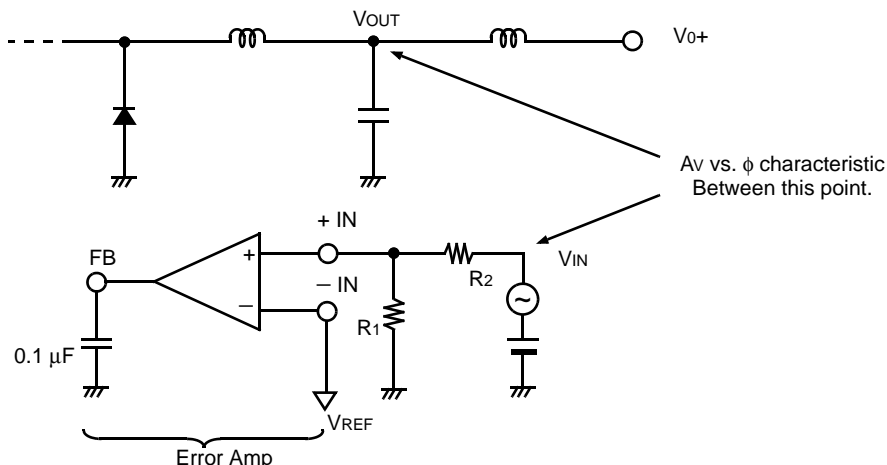


Fig. 33 - DC/DC Converter +5 V Gain/Phase vs. Frequency

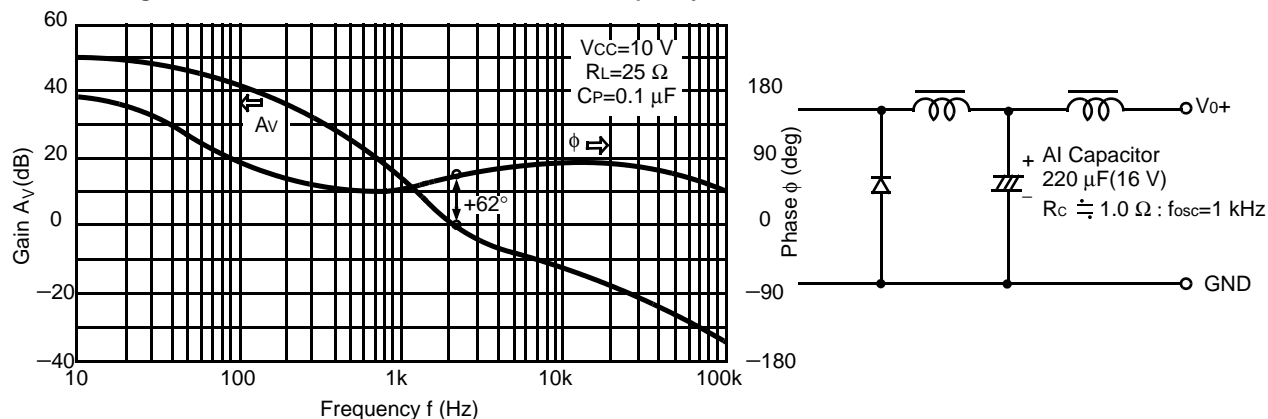
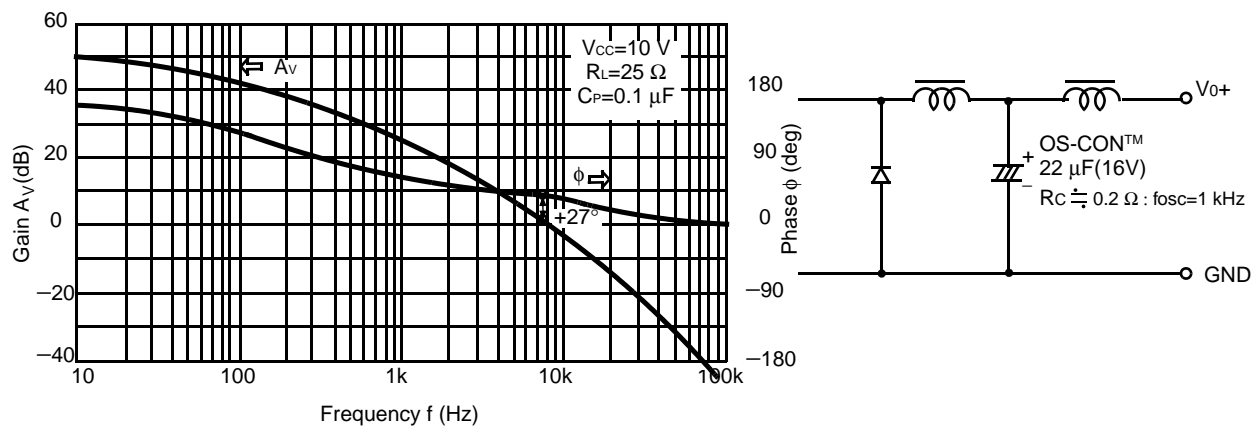


Fig. 34 - DC/DC Converter +5 V Gain/Phase vs. Frequency



MEASURES FOR ENSURING SYSTEM STABILITY WHEN A LOW ESR SMOOTHING CAPACITOR IS USED

When a low ESR smoothing capacitor is used in the DC/DC converter, only the L and C are apparent even in the high-frequency region, and the phase is delayed by almost 180°. Consequently, the system phase margin and stability are reduced. On the other hand, a low ESR capacitor is needed to reduce the amount of output ripple. This is contrary to the system stability explained above.

To solve this problem, phase compensation can be used. This method increases the phase margin by advancing the phase when the phase margin is reduced by a low ESR capacitor.

The three suggestions listed below are recommended for DC/DC converters using the MB3775.

- (1) As shown in Fig. 35, a capacitor is connected in parallel with the output feedback resistor to advance the phase. Use the formula below as a guideline for the capacitance.

$$C1 \div \frac{1}{2\pi f R2}$$

↑
Unstable Frequency (See Fig. 32)

Fig. 35 - External circuit example1 to advance the phase

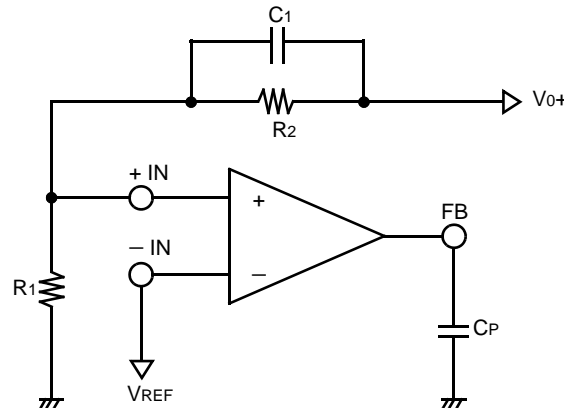
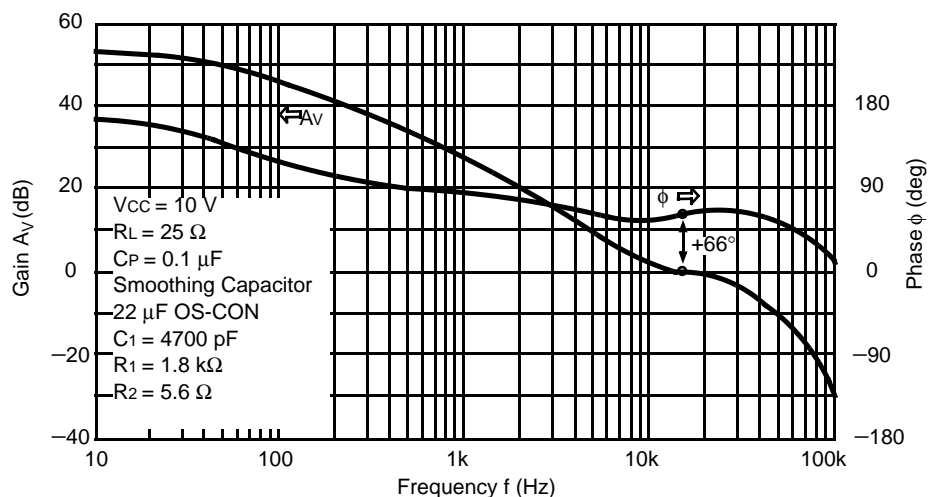
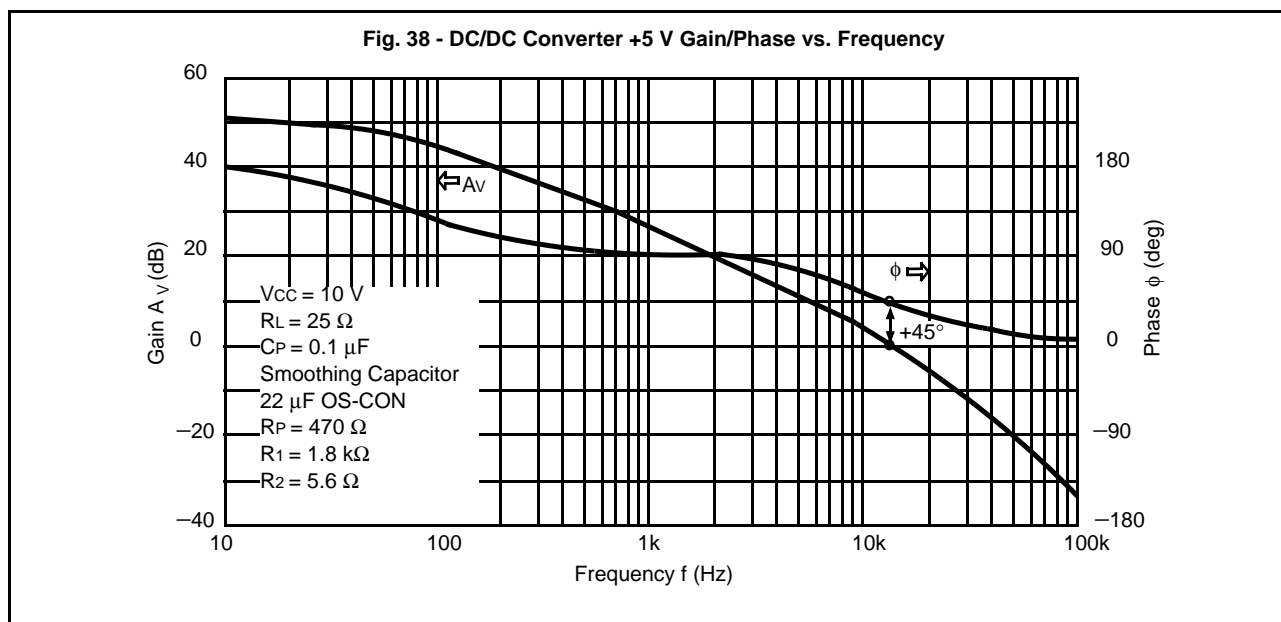
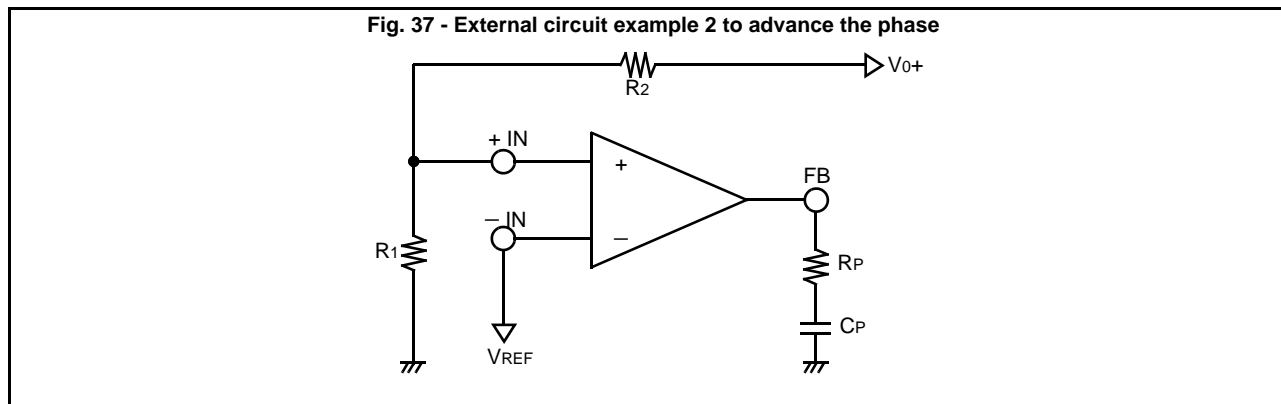


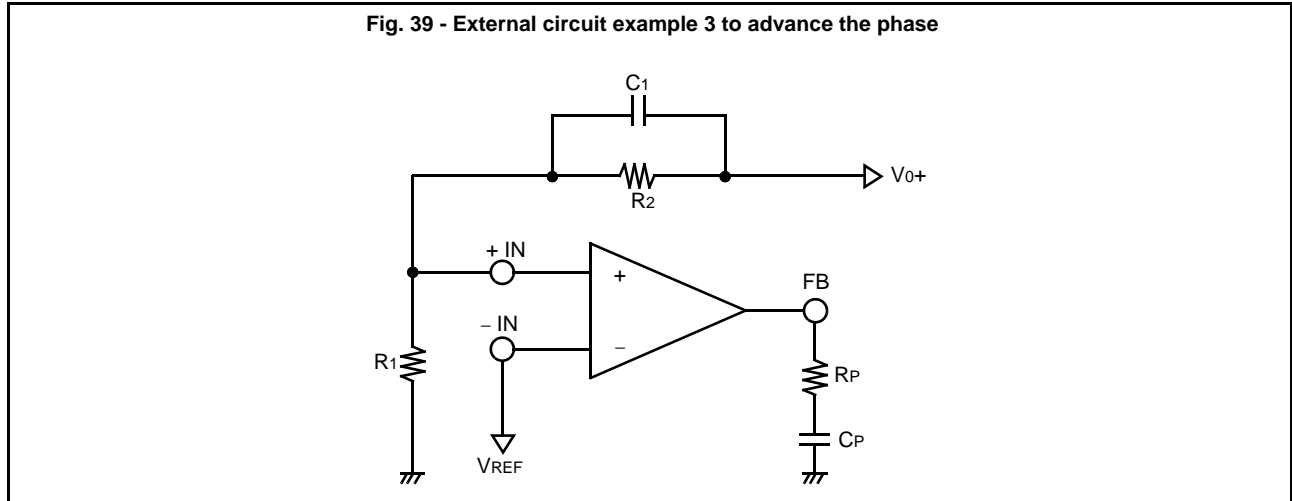
Fig. 36 - DC/DC Converter +5 V Gain/Phase vs. Frequency



- (2) As shown in Figure 37, a resistor (R_P) is connected between the FB terminal (pins 5 and 12) and C_P of the error amplifier to advance the phase. The more R_P is increased, the more the phase is advanced. However, the gain in the high-frequency range is also increased, which causes instability. Therefore, select the optimum resistance (see Fig. 38).



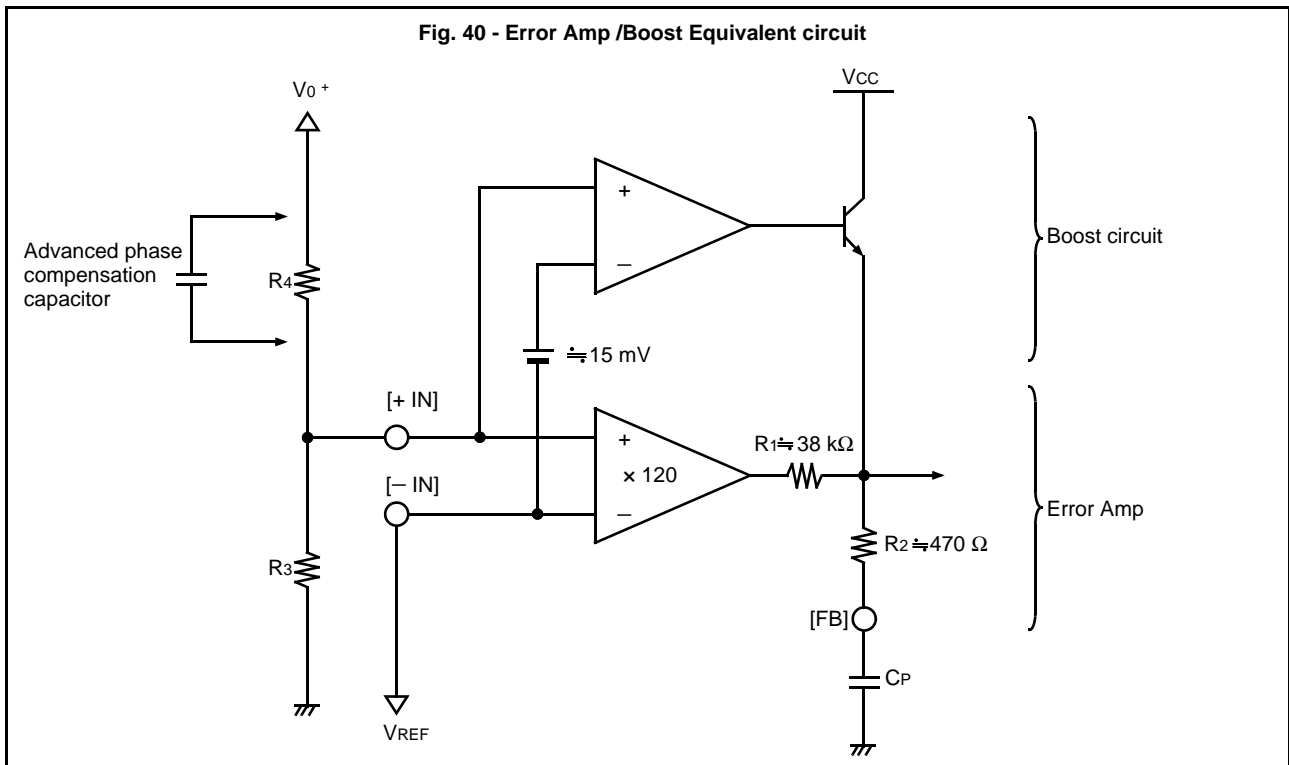
(3) As shown in Fig. 39, the phase is advanced by using both example 1 and 2 (Fig. 35 and 37).



■ ERROR AMPLIFIER INPUT RIPPLE VOLTAGE

The boost circuit for charging the phase compensating capacitor C_P is connected to the error amplifier as shown in Figure 40 to protect against output voltage overload at power-on.

A ≈ 15 mV offset voltage is provided for the negative input side so that the boost circuit only operates at power-on. When a capacitor is connected in parallel with the output feedback resistor, because the output ripple is too large or for advanced phase compensation, the boost circuit starts operating, which may degrade regulation if the differential input voltage of the error amplifier exceeds ≈ 15 mV. Be careful with the differential input voltage of the error amplifier.



MB3775

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■ NOTES ON USE

- Take account of common impedance when designing the earth line on a printed wiring board.
- Take measures against static electricity.
 - For semiconductors, use antistatic or conductive containers.
 - When storing or carrying a printed circuit board after chip mounting, put it in a conductive bag or container.
 - The work table, tools and measuring instruments must be grounded.
 - The worker must put on a grounding device containing 250 kΩ to 1 MΩ resistors in series.
- Do not apply a negative voltage
 - Applying a negative voltage of -0.3 V or less to an LSI may generate a parasitic transistor, resulting in malfunction.

■ ORDERING INFORMATION

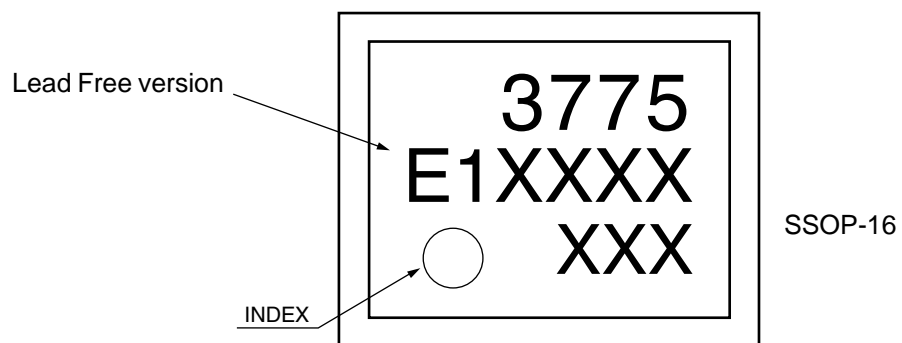
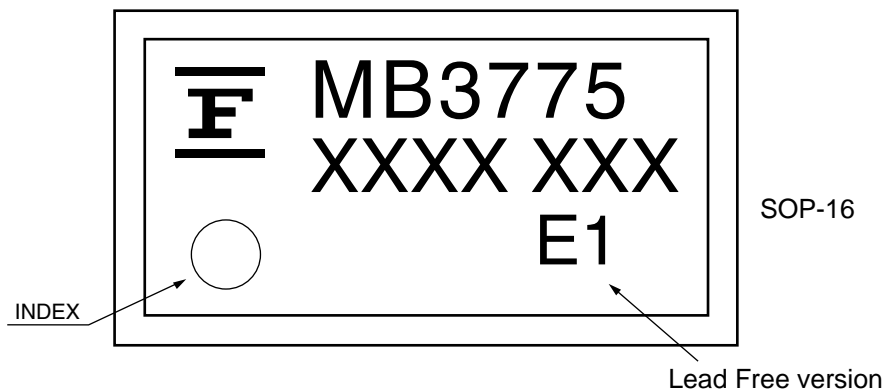
Part number	Package	Remarks
MB3775PF-□□□	16-pin plastic SOP (FPT-16P-M06)	Conventional version
MB3775PFV-□□□	16-pin plastic SSOP (FPT-16P-M05)	Conventional version
MB3775PF-□□□E1	16-pin plastic SOP (FPT-16P-M06)	Lead Free version
MB3775PFV-□□□E1	16-pin plastic SSOP (FPT-16P-M05)	Lead Free version

■ RoHS Compliance Information of Lead (Pb) Free version

The LSI products of Fujitsu with "E1" are compliant with RoHS Directive , and has observed the standard of lead, cadmium, mercury, Hexavalent chromium, polybrominated biphenyls (PBB) , and polybrominated diphenyl ethers (PBDE) .

The product that conforms to this standard is added "E1" at the end of the part number.

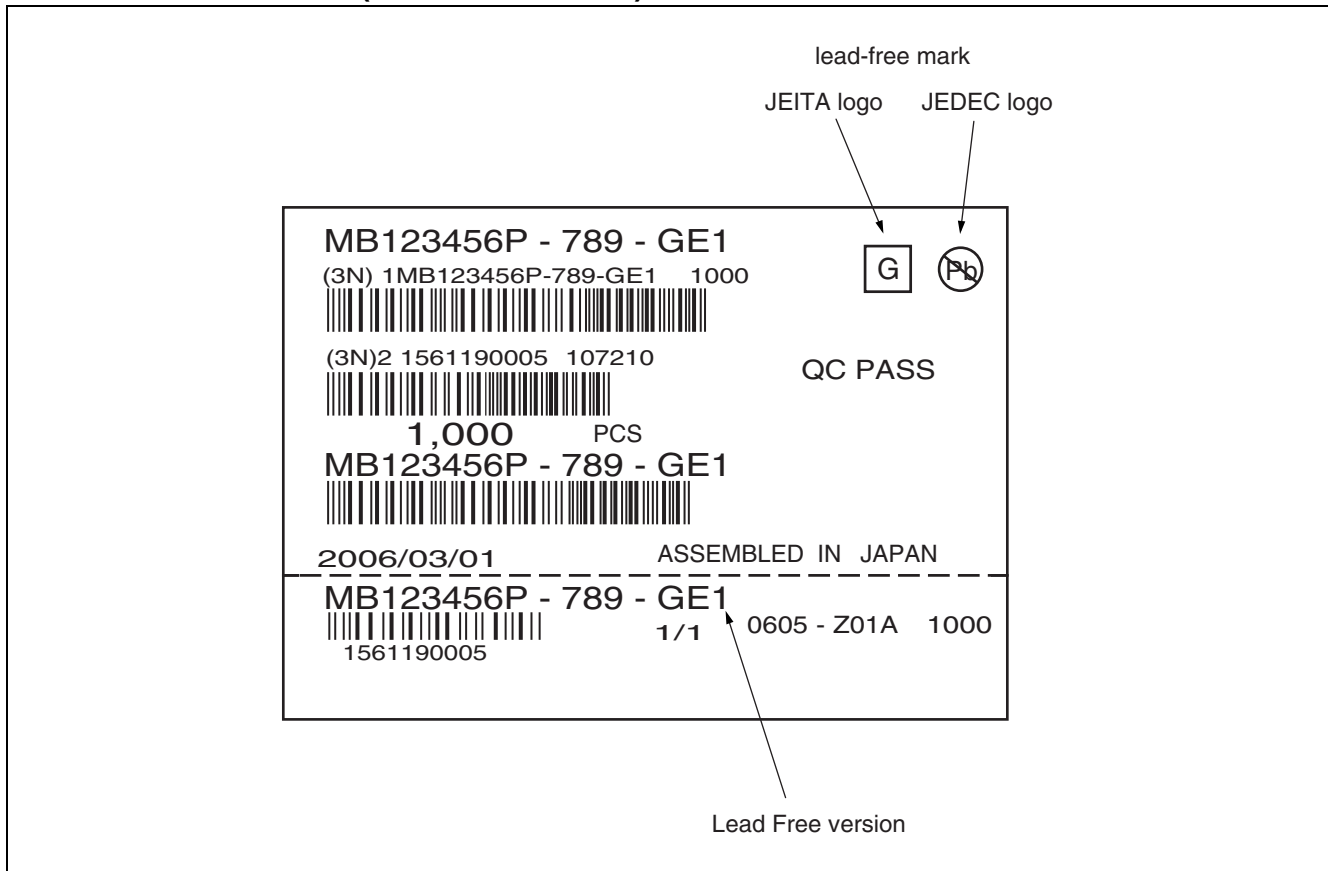
■ MARKING FORMAT (Lead Free version)



MB3775

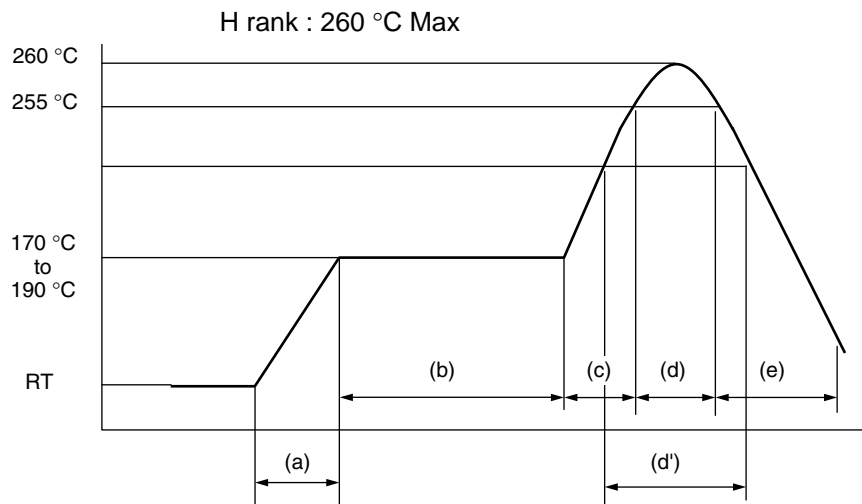
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■ LABELING SAMPLE (Lead free version)



Item	Condition	
Mounting Method	IR (infrared reflow) , Manual soldering (partial heating method)	
Mounting times	2 times	
Storage period	Before opening	Please use it within two years after Manufacture.
	From opening to the 2nd reflow	Less than 8 days
	When the storage period after opening was exceeded	Please processes within 8 days after baking (125 °C, 24H)
Storage conditions	5 °C to 30 °C, 70%RH or less (the lowest possible humidity)	

(1) IR (infrared reflow)



- (a) Temperature Increase gradient : Average 1 °C/s to 4 °C/s
- (b) Preliminary heating : Temperature 170 °C to 190 °C, 60s to 180s
- (c) Temperature Increase gradient : Average 1 °C/s to 4 °C/s
- (d) Actual heating : Temperature 260 °C Max; 255 °C or more, 10s or less
- (d') : Temperature 230 °C or more, 40s or less
or
Temperature 225 °C or more, 60s or less
or
Temperature 220 °C or more, 80s or less
- (e) Cooling : Natural cooling or forced cooling

Note : Temperature : the top of the package body

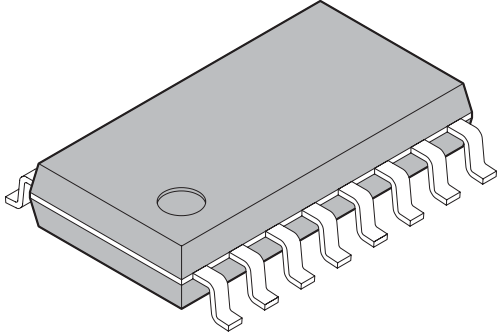
Conditions : Temperature 400 °C Max

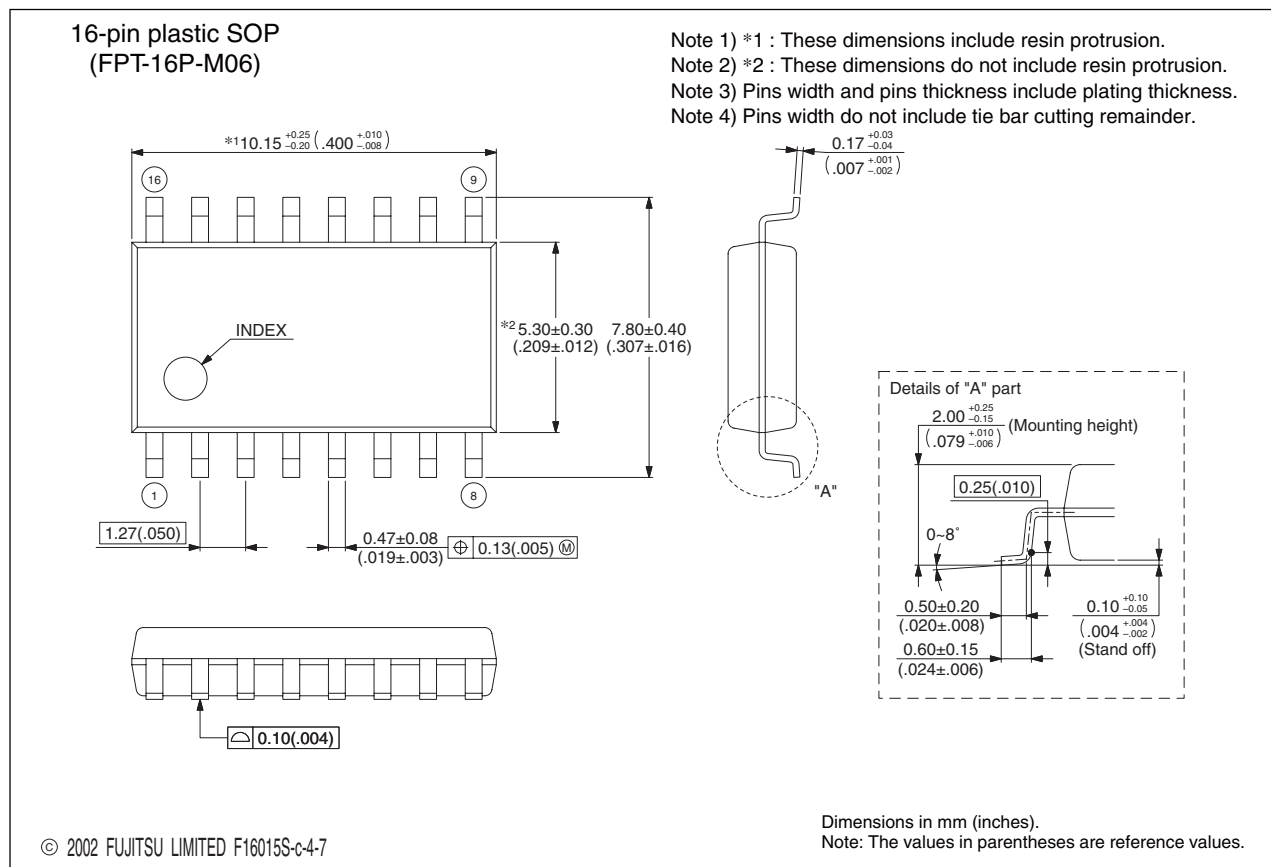
Times : 5 s max/pin

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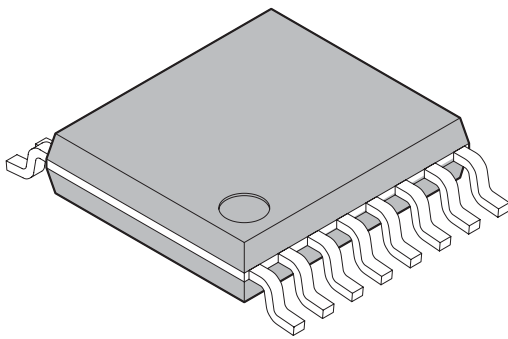
■ PACKAGE DIMENSION

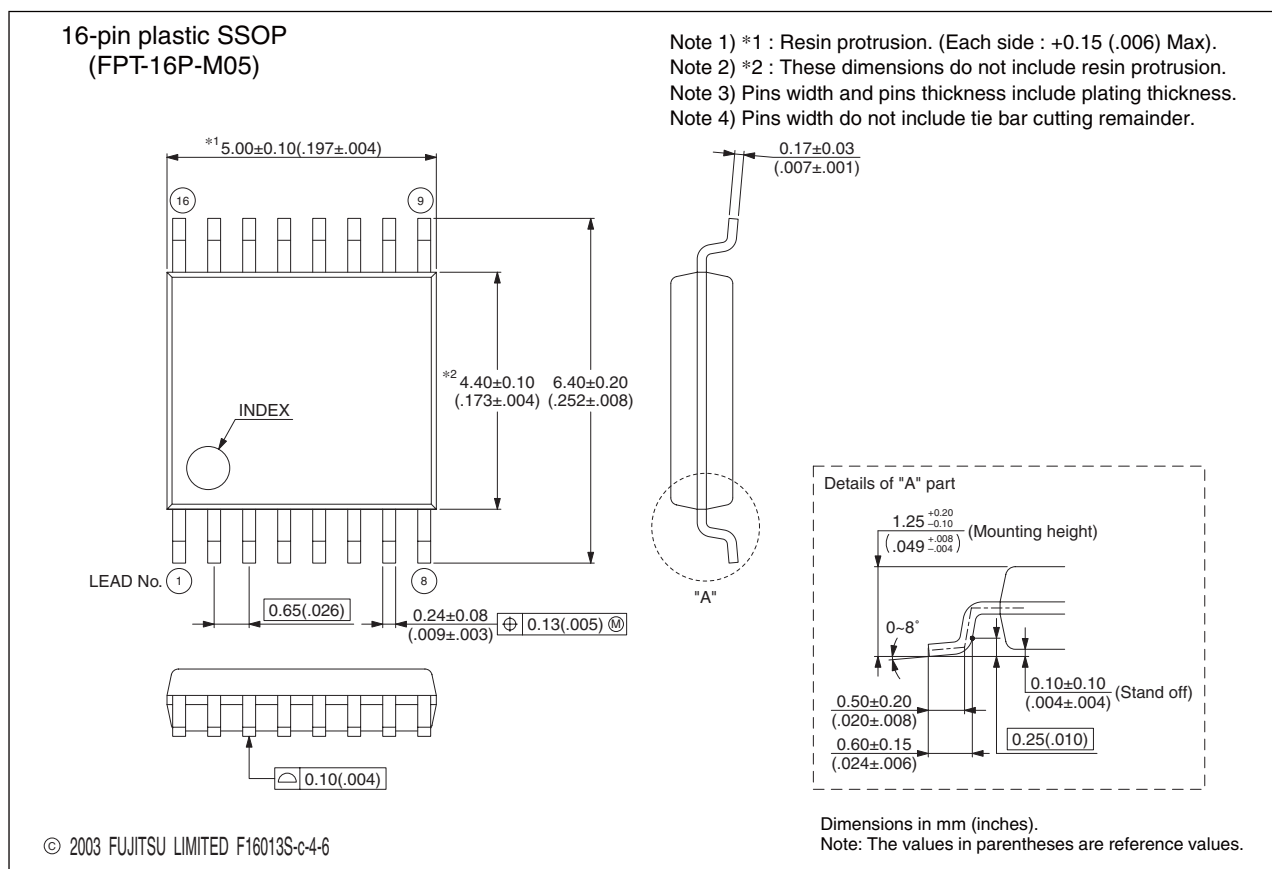
<p>16-pin plastic SOP</p>  <p>(FPT-16P-M06)</p>	Lead pitch	1.27 mm
	Package width × package length	5.3 × 10.15 mm
	Lead shape	Gullwing
	Sealing method	Plastic mold
	Mounting height	2.25 mm MAX
	Weight	0.20 g
	Code (Reference)	P-SOP16-5.3×10.15-1.27



(Continued)

(Continued)

<p>16-pin plastic SSOP</p>  <p>(FPT-16P-M05)</p>	Lead pitch	0.65 mm
	Package width × package length	4.40 × 5.00 mm
	Lead shape	Gullwing
	Sealing method	Plastic mold
	Mounting height	1.45mm MAX
	Weight	0.07g
	Code (Reference)	P-SSOP16-4.4×5.0-0.65



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